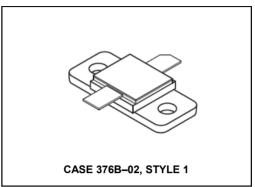


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Designed for 1025–1150 MHz pulse common base amplifier applications such as TCAS, TACAN and Mode–S transmitters.

- Guaranteed performance @ 1090 MHz
   Output power = 150 W Peak
   Gain = 9.5 dB min, 10.0 dB (typ.)
- 100% tested for load mismatch at all phase angles with 10:1 VSWR
- Hermetically sealed package
- Silicon nitride passivated
- Gold metallized, emitter ballasted for long life and resistance to metal migration
- Internal input and output matching
- Characterized with 10 μs, 10% duty cycle pulses
- Recommended driver for a pair of MRF10500 transistors

### Product Image



#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CES</sub>	65	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	65	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	3.5	Vdc
Collector Current — Peak (1)	I <sub>C</sub>	14	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C (1), (2) Derate above 25°C	P <sub>D</sub>	700 4.0	Watts W/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +200	°C
Junction Temperature	TJ	200	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	R <sub>θJC</sub>	0.25	°C/W

#### NOTES

- 1. Under pulse RF operating conditions.
- These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.
- Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst case θ<sub>JC</sub> value measured @ 10 μs, 10%.)

1

### MRF10150



# Microwave Pulse Power Silicon NPN Transistor 150W (peak), 1025–1150MHz

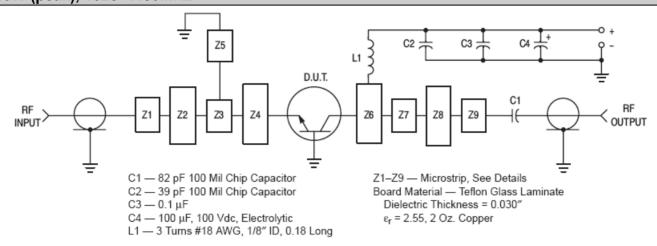
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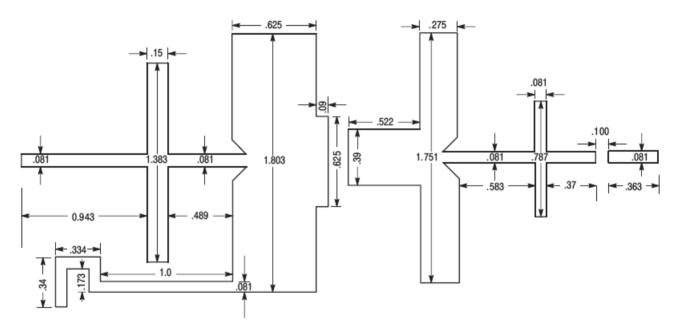
#### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 60 mAdc, V <sub>BE</sub> = 0)	V <sub>(BR)CES</sub>	65	_	_	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 60 mAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	65	_	_	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 mAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	3.5	_	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 36 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	_	25	mAdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	20	_	_	_
FUNCTIONAL TESTS					
Common–Base Amplifier Power Gain (V <sub>CC</sub> = 50 Vdc, P <sub>out</sub> = 150 W Peak, f = 1090 MHz)	G <sub>PB</sub>	9.5	10	_	dB
Collector Efficiency (V <sub>CC</sub> = 50 Vdc, P <sub>out</sub> = 150 W Peak, f = 1090 MHz)	η	40	_	_	%
Load Mismatch (V <sub>CC</sub> = 50 Vdc, P <sub>out</sub> = 150 W Peak, f = 1090 MHz, VSWR = 10:1 All Phase Angles)	Ψ	No Degradation in Output Power			



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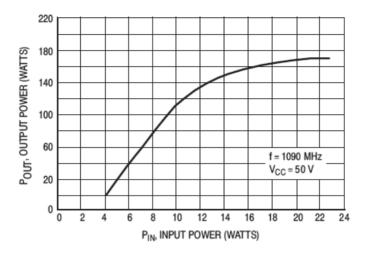
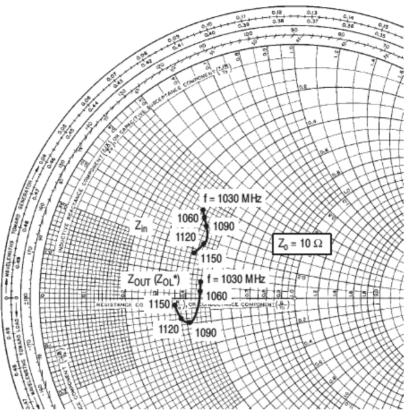


Figure 2. Output Power versus Input Power



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 $P_{OUT} = 150 \text{ W Pk}$   $V_{CC} = 50 \text{ V}$ 

001					
f MHz	Z <sub>in</sub> OHMS	Z <sub>OL*</sub> (Z <sub>OUT</sub> ) OHMS			
1030	3.8 + j3.5	4.6 + j0.7			
1060	4.0 + j3.3	4.6 + j0.3			
1090	4.2 + j3.0	4.1 – j1.0			
1120	4.4 + j2.3	3.8 - j0.8			
1150	4.1 + j1.8	3.6 - j0.3			

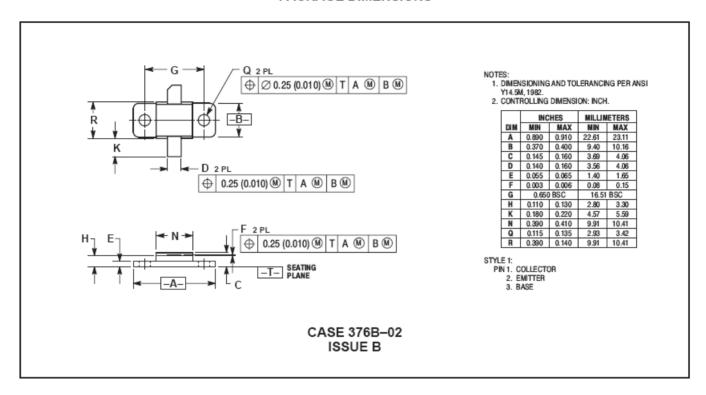
Z<sub>OL</sub>\* is the conjugate of the optimum load impedance into which the device operates at a given output power voltage and frequency.

Figure 3. Series Equivalent Input/Output Impedances



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#### PACKAGE DIMENSIONS



### MRF10150



Microwave Pulse Power Silicon NPN Transistor 150W (peak), 1025–1150MHz

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